

WHAT IS CLAIMED IS:

1. A manufacturing method of a semiconductor apparatus, comprising the steps of:

forming a mask material film made of organic insulation film
5 on a film to be processed;

forming a tapered aperture pattern, in which a bottom of said aperture pattern is made narrower than an open side of said aperture pattern on said mask material film; and

etching said film to be processed by using said mask material
10 film as a mask.

2. The manufacturing method of a semiconductor apparatus according to claim 1, further including the step of removing said mask material film.

3. The manufacturing method of a semiconductor
15 apparatus according to claim 1, wherein said film to be processed has a step.

4. The semiconductor apparatus manufacturing method according to claim 1, wherein
said mask material film is made of material having a low
20 dielectric constant.